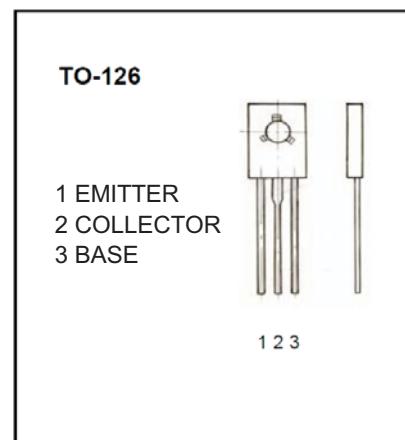


PNP Epitaxial Silicon Transistor

BD436

■ Features

- Medium Power Linear and Switching Applications



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	-32	V
Collector-Emitter Voltage	V _{CES}	-32	V
Collector-Emitter Voltage	V _{CEO}	-32	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current (DC)	I _C	-4	A
Collector Current (Pulse) *	I _{CP}	-7	A
Base Current	I _B	-1	A
Collector Dissipation (TC=25°C)	P _C	36	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{TSG}	-65 to 150	°C

* Pulse Test: PW=300μs, duty Cycle=1.5% Pulsed

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Emitter Sustaining Voltage	V _{CEO}	I _C = -100mA, I _B = 0	-32			V
Base-Emitter ON Voltage *	V _{BE(on)}	V _{CE} = -1V, I _C = -2A			-1.1	V
Collector Cut-off Current	I _{CBO}	V _{CB} = -32V, I _E = 0			-100	μ A
Collector Cut-off Current	I _{CEO}	V _{CE} = -32V, V _{BE} = 0			-100	μ A
Emitter Cut-off Current	I _{EBO}	V _{EB} = -5V, I _C = 0			-1	mA
DC Current Gain *	h _{FE}	V _{CE} = -5V, I _C = -10mA	85		300	
		V _{CE} = -1V, I _C = -500mA	85	140		
		V _{CE} = -1V, I _C = -2A	50			
Collector-Emitter Saturation Voltage *	V _{CE(sat)}	I _C = -2A, I _B = -0.2A		-0.2	-0.5	V
Transition frequency	f _T	V _{CE} = -1V, I _C = -250mA	3			MHz

* Pulse Test: PW=300 μ s, duty Cycle=1.5% Pulsed